- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

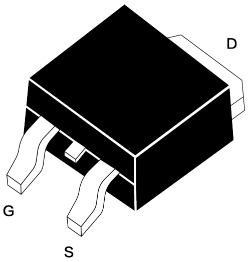
BVDSS	RDSON	ID
100V	20 mΩ	40A

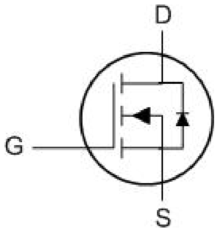
Description

The JHS40N10 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The JHS40N10 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO-252 Pin Configuration





Absolute Maximum Ratings T_C=25℃ unless otherwise specified

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		100	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current note5	T_C = 25℃	40	A
I_D	Continuous Drain Current note5	T_C = 100℃	16	A
I_{DM}	Pulsed Drain Current note3		100	A
P_D	Power Dissipation note2	T_C = 25℃	27	W
I_{AS}	Avalanche Current note3,6		8	A
E_{AS}	Single Pulse Avalanche Energy note3,6		16	mJ
$R_{\theta JC}$	Thermal Resistance, Junction to Case		4.65	℃/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient note1,4		62	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

Electrical Characteristics T_C=25℃ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	100	-	-	V
I_{DSS}	Drain-Source Leakage Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	1.2	1.8	2.6	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10V, I_D = 15A	-	20	23	mΩ
		V_{GS} = 4.5V, I_D = 10A	-	-	33	mΩ
g_{fs}	Forward Threshold Voltage	V_{DS}= 10V, I_D= 20A	-	22	-	S
R_g	Gate Resistance	V_{DS} = V_{GS}=0V, f = 1.0MHz	-	1.62	-	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 50V, V_{GS} = 0V, f = 1.0MHz	-	822	-	pF
C_{oss}	Output Capacitance		-	310	-	pF
C_{rss}	Reverse Transfer Capacitance		-	23.5	-	pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS}= 50V, I_D = 20A, V_{GS} = 10V	-	22.7	-	nC
Q_{gs}	Gate-Source Charge		-	6.2	-	
Q_{gd}	Gate-Drain(“Miller”) Charge		-	5.3	-	
$t_{d(on)}$	Turn-On Delay Time	V_{DS} = 50V, I_D = 20A, R_G = 3Ω, V_{GS}=10V	-	15	-	ns
t_r	Turn-On Rise Time		-	3.2	-	
$t_{d(off)}$	Turn-Off Delay Time		-	30	-	
t_f	Turn-Off Fall Time		-	7.6	-	
Diode Characteristics						
I_S	Continuous Source Current		-	-	40	A
V_{SD}	Diode Forward Voltage	I_S=20A . V_{GS} = 0V	-	0.88	1.0	V
t_{rr}	Reverse Recovery Time	I_{SD}=20A, dI_{SD}/dt=100A/μs	-	45	-	ns
Q_{rr}	Reverse Recovery Charge		-	59	-	nC

Notes:

1. The value of $R_{θJC}$ is measured in a still air environment with TA =25°C and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
2. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
3. Single pulse width limited by junction temperature $T_{J(MAX)}$=150°C.
4. The $R_{θJA}$ is the sum of the thermal impedance from junction to case $R_{θJC}$ and case to ambient.
5. The maximum current rating is package limited.
6. The EAS data shows Max. rating. The test condition is V_{DS}=50V,V_{GS}=10V,L=0.5mH

Typical Performance Characteristics

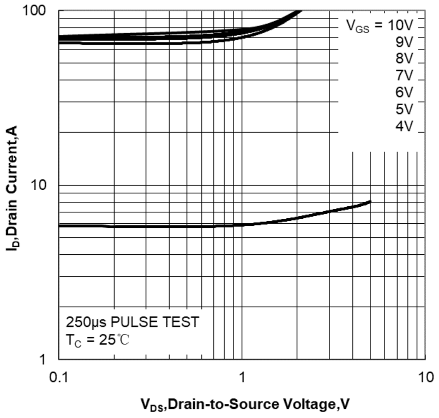


Figure 1. Output Characteristics

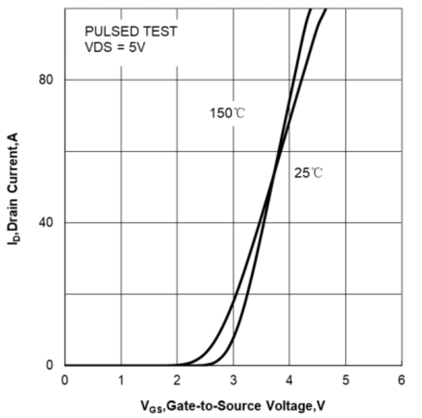


Figure 2. Transfer Characteristics

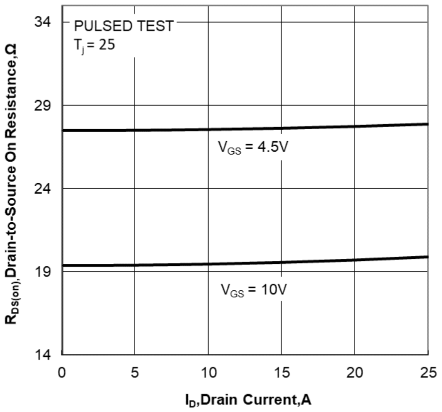


Figure 3. Drain-to-Source On Resistance vs Drain Current

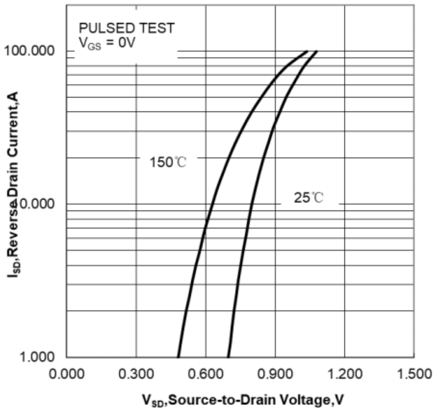


Figure 4. Body Diode Forward Voltage vs Source Current and Temperature

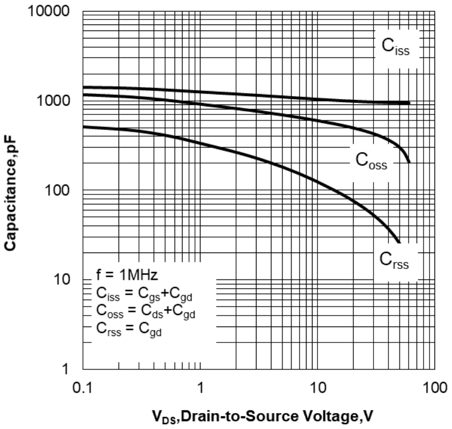


Figure 5. Capacitance Characteristics

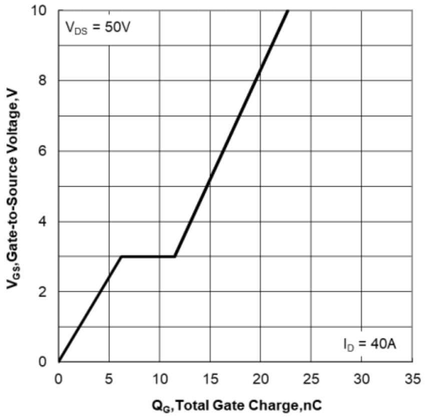


Figure 6. Gate Charge Characteristics

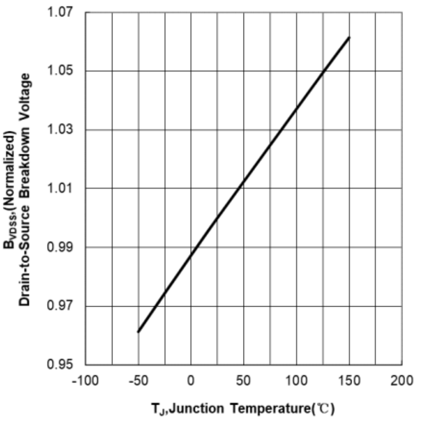


Figure 7. Normalized Breakdown Voltage vs Junction Temperature

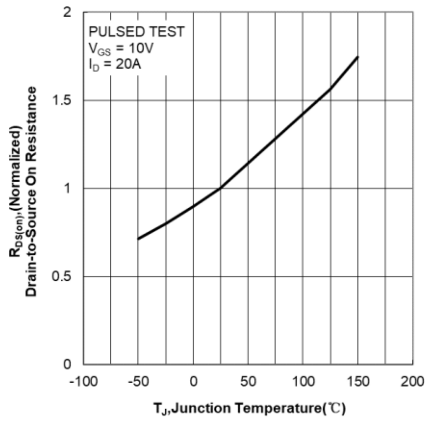


Figure 8. Normalized On Resistance vs Junction Temperature

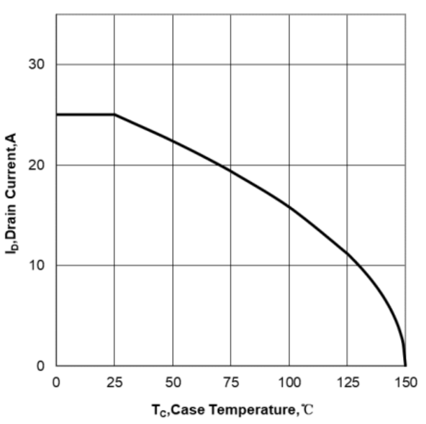


Figure 9. Maximum Continuous Drain Current vs Case Temperature

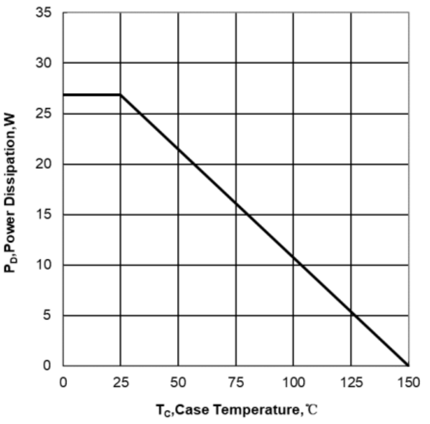


Figure 10. Maximum Power Dissipation vs Case Temperature

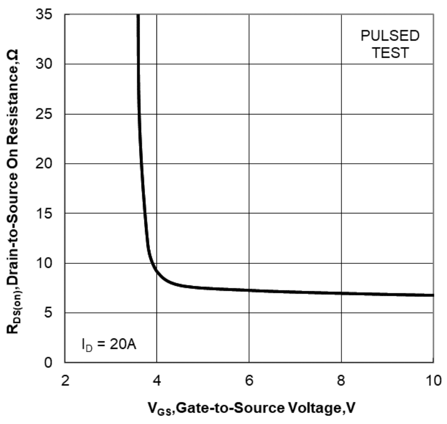


Figure11. Drain-to-Source On Resistance vs Gate

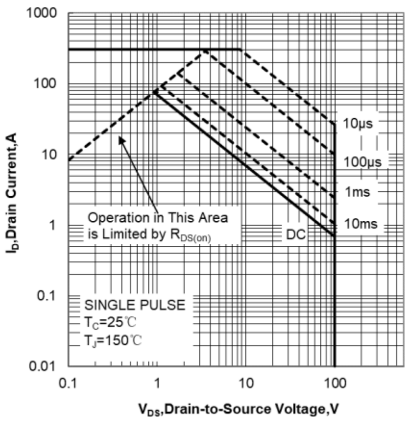


Figure 12. Maximum Safe Operating Area

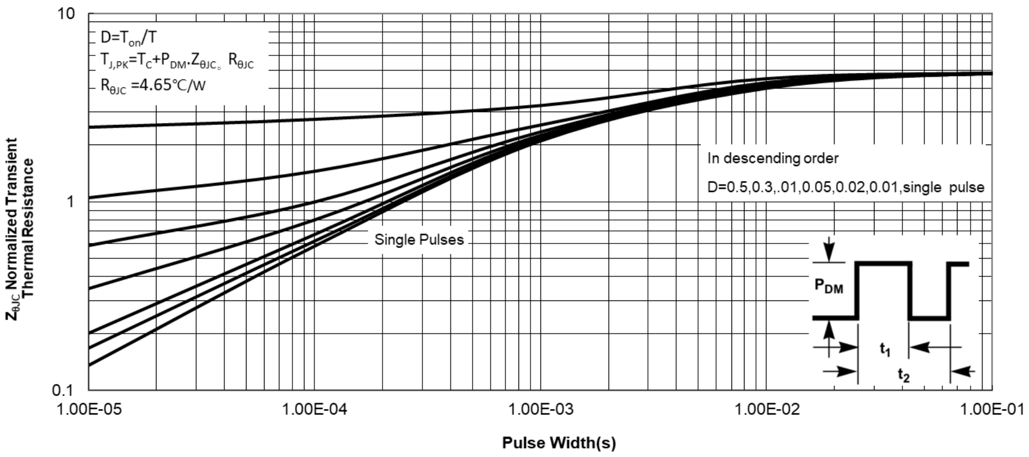
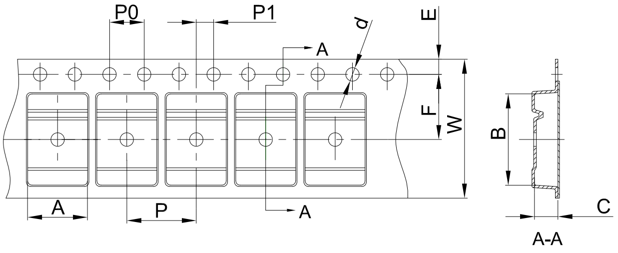


Figure 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

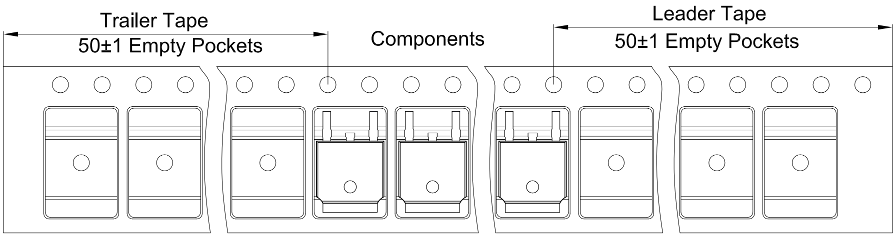
TO-252-2L Tape and Reel

TO-252 Embossed Carrier Tape

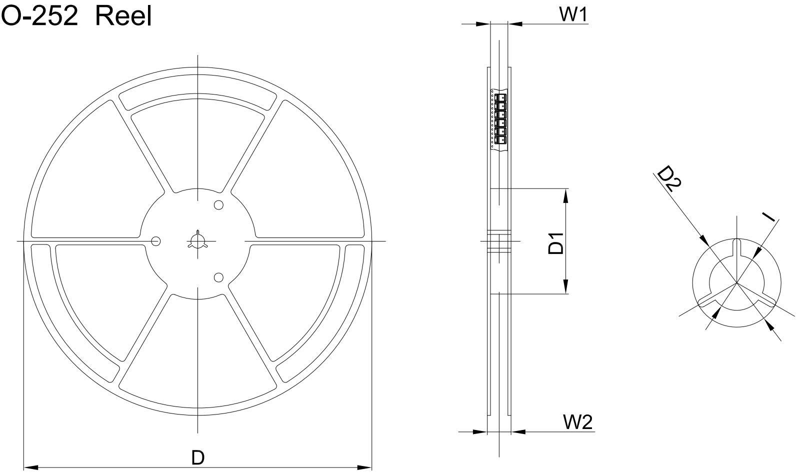


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
TO-252	6.90	10.50	2.70	Ø1.55	1.75	7.50	4.00	8.00	2.00	16.00

TO-252 Tape Leader and Trailer

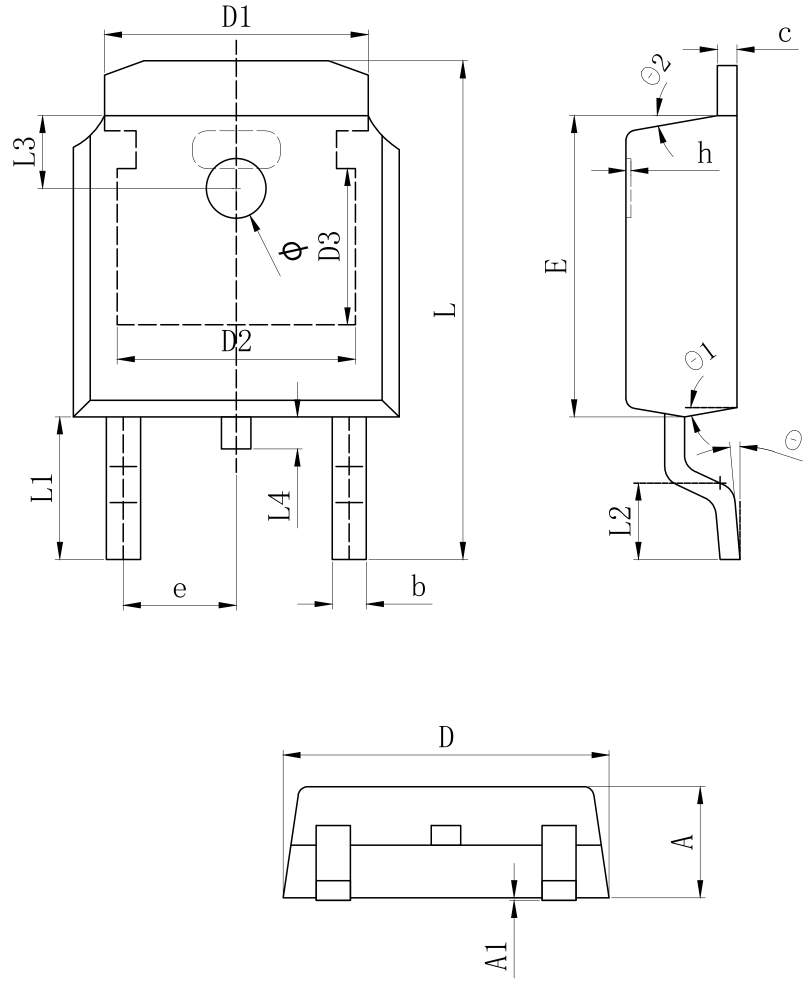


TO-252 Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	W1	W2	I
13"Dia	330.00	100.00	Ø21.00	16.40	21.00	Ø13.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
2,500 pcs	13inch	2,500 pcs	340×336×29	25,000 pcs	353×346×365	



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		

DISCLAIMER

JHG PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with JHG products. You are solely responsible for

(1)selecting the appropriate JHG products for your application;

(2)designing, validating and testing your application;

(3)ensuring your application meets applicable standards, and any other safety, security, or other requirements.

These resources are subject to change without notice. JHG grants you permission to use these resources only for development of an application that uses the JHG products described in the resource. Other reproduction and display of these resources are prohibited. No license is granted to any other JHG intellectual property right or to any third party intellectual property right. JHG disclaims responsibility for, and you will fully indemnify JHG and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.